

October 21 (Wed.), 2026

Poster Session

13:00-15:10

Gallery (1F)

■ 01. Advanced Interconnect CMP (Metal)

- ★[P-001] [Achieving High-Selectivity Tungsten Planarization at Neutral pH via Poly-L-Lysine Inhibition](#)

[Hyunho Kim](#), Chaerin Park, and Taesung Kim (Sungkyunkwan Univ., Korea)

- [P-002] [Copper CMP Slurry Tailored for Applications with Different Dimensions](#)

[Ping Tzeng](#), [Jingzhi Chen](#) (Merck Performance Materials Ltd. - Hsinchu Site, Taiwan), and [Hongjun Zhou](#) (Merck KGaA, Germany)

- [P-003] [New Ceria CMP Slurry Designs for High Throughput Selective Metal TSV Applications](#)

[Wei Hisn \(Howl\) Hsu](#), [Chien-Liang \(Mason\) Liu](#), and [Long Dai Lu](#) (Entegris, Inc., Taiwan)

- ★[P-004] [Synergistic Effect of 1,2,4-Triazole and Polymers on Copper Chemical Mechanical Polishing](#)

[Jiaxin Zheng](#), [Yongshun Zhang](#), [Yuting Wei](#), [Liao Zhou](#), [Qiuyu Li](#), [Hui Li](#) (Southwest Jiaotong Univ., China), [Liang Jiang](#) (Southwest Jiaotong Univ. & Yanghua Zhizao (Sichuan) Innovation Technologies Co., Ltd., China), and [Linmao Qian](#) (Southwest Jiaotong Univ., China)

- [P-005] [Multiple Synergistic Effects of a Novel PVP-Optimized Slurry System in Mediating Atomic-Scale Synchronous Polishing of Cobalt Interconnection Heterostructures](#)

[Zixin Gao](#) (Hwatsing Tech. Co., Ltd., China), [LIFEI Zhang](#), [Xinchun Lu](#), and [Jialei](#)

Zhang (Tsinghua Univ., China)

■ 02. Dielectric & Hard materials CMP

[P-006] [Effect of Ceria Residue on STI Polishing](#)

Ying-Chieh Chao, Toshio Shinoda, Takahiro Umeda, and Yasuto Ishida (Fujimi Taiwan Ltd., Taiwan)

[P-007] [Precise Calculation Method for Oxide CMP APC Pressure Tuning](#)

Qidong Zhang, Hung-Chieh Chao, Chang Hung, Kung, and Kaiqiang Wang (Sien Integrated Circuit Co., Ltd., China)

★[P-008] [Selectivity Enhancement Mechanism in STI CMP Using Ceria Abrasives](#)

Chaerin Park, Jeongbin Kim, and Taesung Kim (Sungkyunkwan Univ., Korea)

[P-009] [Next Generation HORS Slurry Development](#)

Yang-Yao Lee and Ming-Che Ho (Vibrant Technologies, USA)

[P-010] [Acceleration of GaN CMP Rate via Ion Implantation](#)

Akira Sada, Sota Ueda, Yuya Uchida, Takeshi Matsumoto (Nissin Ion Equipment Co., Ltd., Japan), and Keisuke Suzuki (Kyushu Inst. of Tech., Japan)

★[P-011] [High-Efficiency Chemical Mechanical Polishing of Polycrystalline Diamond Substrates](#)

Yibo Zhou (Ludong Univ., China), Guanghong Luo (Ludong Univ. & Yantai Xianhua Polymer Materials Co., Ltd., China), and Tao Wang (Shenzhen Polytechnic Univ., China)

★[P-012] [Selective Adsorption of an Imidazole Polymer for Oxide-Stop Nitride CMP](#)

Donggeun Park, Ilhwa Hong, Ganghyeok Kim, Youngmin Kim, Gimok Lee, and Kangchun Lee (Kwangwoon Univ., Korea)

[P-013] [Evaluation and Optimization of CMP Processes for Different GaN Applications](#)

Ahiliya Sen, Patrick Ong, Md Arif Khan, Edoardo Brezza, and Karen Geens
(imec, Belgium)

[P-014] [Surface Processing of Thin Diamond Samples](#)

Robert Rhoades (Kothar Technologies, USA), and John Ciraldo (WD Advanced
Materials, USA)

■ 03. Advanced Packaging / 3D Integration CMP (Hybrid Cu Bonding, BSPDN, Wafer
Thinning)

★[P-015] [Minimizing Selectivity of Cu/SiCN Using Micro-Replicated Pad for Hybrid
Bonding CMP](#)

Ziyang Wang, Yin hao An, Janghyun Kim (Sungkyunkwan Univ., Korea),
Yongsuk Yang, Changwan Bae (3M Korea, Korea), and Taesung Kim
(Sungkyunkwan Univ., Korea)

[P-016] [Asymmetrical Surface Characterization of Bulk Si Post Extreme Thinning for
Advanced 3D Integration Applications](#)

Zouhair Ameghnas and Jakob Visker (imec, Belgium)

★[P-017] [Investigation of Low Selectivity between Amorphous Carbon and Silicon
Nitride of Application in 3D NAND Flash CMP](#)

Janghyun Kim, Ziyang Wang, and Taesung Kim (Sungkyunkwan Univ., Korea)

[P-018] [CMOS-Compatible Gold-Free Tungsten Gate Integration for Graphene THz
Plasmonics on Silicon](#)

Marco Lisker, Ketan Anand, Dirk Hagen, Awwal Adeniyi Adesunkanmi,
Andreas Krüger (IHP GmbH - Leibniz Inst. for High Performance
Microelectronics, Germany), and Andreas Mai (IHP GmbH - Leibniz Inst. for
High Performance Microelectronics & Technical Univ. of Applied Sciences
Wildau, Germany)

[P-019] [Selectivity Control in IC Slurry Design for Advanced Packaging](#)

[Francis Acquaye](#), Sudeep Kuttiatoor, Jay Chang, and Alex Hains (Entegris, Inc., USA)

★[P-020] [Study on the Effect of Fe-Based Fenton Reaction on Amorphous Carbon Removal in CMP](#)

[Yinhao An](#), Ziyang Wang, and Taesung Kim (Sungkyunkwan Univ., Korea)

★[P-021] [Effect of Grain Size on Cu CMP-Induced Surface Evolution for Controlled Low-Temperature Hybrid Bonding](#)

[Donghwan Choi](#), Hyeonjeong Lee, Hyunkyu Kim (Sungkyunkwan Univ., Korea), Sungho Park, Yunhee Cho (BASF Company Ltd., Korea), Andreas Klipps (BASF SE, Germany), and Taesung Kim (Sungkyunkwan Univ., Korea)

★[P-022] [Structural Optimization of Surface-Structured Pads for Reducing Pattern-to-Pattern Variation in Cu Dishing](#)

[Jeongseok Oh](#), Gunhoo Park, Sukkyung Kang, Dong Geun Kim, and Sanha Kim (KAIST, Korea)

[P-023] [High-Selectivity, High-Rate Polyimide CMP Assisted by Functionalized Structured Pads for Cu/Polymer Hybrid Bonding](#)

[Il Ryu Jang](#), Seounghee Yun, Jiseung Lee, Joohyun Park, Hyunwoong Baek, Sukkyung Kang, and Sanha Kim (KAIST, Korea)

★[P-024] [Diethylenetriamine-Induced Opposite Surface Responses of Cu and Borosilicate Glass for High-Selectivity TGV CMP](#)

[Hyunkyu Kim](#), Jongyeong Jeon, Janghyun Kim (Sungkyunkwan Univ., Korea), and Yoojin Son (Samsung Electronics Co., Ltd., Korea), Taesung Kim (Sungkyunkwan Univ., Korea)

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- ★[P-025] [Pressure-Driven Selectivity Inversion in Cu/SiCN CMP for Advanced Hybrid Bonding](#)

Jeongbin Kim, Chaerin Park, and Taesung Kim (Sungkyunkwan Univ., Korea)

- [P-026] [DTW CMP Process Exploration and Optimization](#)

Damien Hebras, Renan Bouis, Arnaud Cornelis, and Catherine Euvrard (Univ. Grenoble Alpes, CEA-Leti, France)

- [P-027] [Modeling of Cu Dishing based on Asperity-Level Micro-Contact Mechanics for Cu/SiO₂ Hybrid Bonding](#)

Seong Jae Kim, Yoon Sick Eom, Hyeonseo Han, Kyunghyun Kim, Jeongseok Oh, Gunhoo Park, Hyun Jun Ryu, and Sanha Kim (KAIST, Korea)

- ★[P-028] [Chemical Mechanical Polishing of Semi-Cured BCB for Cu/Polymer Hybrid Bonding with High Bonding Strength](#)

Joohyun Park, Sukkyung Kang, Il Ryu Jang, Hyunwoong Baek, Jiseung Lee, Chansu Jeon, Kyung Min Kim, and Sanha Kim (KAIST, Korea)

- ★[P-029] [Graphene-integrated Cu CMP for Cu/SiO₂ Hybrid Bonding](#)

Jumin Ahn, Jinhyoung Lee, Gunhyoung Kim, and Taesung Kim (Sungkyunkwan Univ., Korea)

- ★[P-030] [APTES-Modified SiO₂ Abrasives for Low-Defect AlN CMP](#)

Ganghyeok Kim, Donggeun Park, Ilhwa Hong, Youngmin Kim, Gimok Lee, and Kangchun Lee (Kwangwoon Univ., Korea)

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- ★[P-031] [Mechanistic Insights into Cu/borosilicate Glass CMP and Selectivity Control for through-Glass via \(TGV\)](#)

Jonyeong Jeon, Chaerin Park, Juyeol Lee, and Taesung Kim (Sungkyunkwan Univ., Korea)

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- ★[P-032] [CMP Study of Redistribution Layer \(RDL\) Using Build-Up Films \(BUF\) and Photo-Imageable Dielectrics \(PID\) for Advanced Packaging](#)

Eunok Kim, Boyeong Hwang, Jinmyeong Hwang, Jaehak Lee, Seungmahn Lee, and Jaedong Lee (KCTech, Korea)

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- ★[P-033] [pH-Controlled ZrO₂ Slurry for Chemical Mechanical Polishing of Polyimide Film](#)

Yechan Kim, Jongyeong Jeon, and Taesung Kim (Sungkyunkwan Univ., Korea)

■ 04. Post-CMP Cleaning / Defect Engineering

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- ★[P-034] [Investigation on Silica Particle Cleaning Mechanism of Surfactants for Amorphous Carbon Post-CMP Cleaning](#)

Minha Kim, Ziyang Wang, and Taesung Kim (Sungkyunkwan Univ., Korea)

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- ★[P-035] [Visualization Method of Near Surface Liquid Replacement Induced by Deformation of a PVA Brush](#)

Makoto Miwa (Shizuoka Univ., Japan), Tomoya Nishi (Ebara Corp., Japan), and Toshiyuki Sanada (Shizuoka Univ., Japan)

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- [P-036] [A Comparative Evaluation of THEMAH as a Potential Alternative to TMAH in Cu Post-CMP Cleaning Solutions](#)

Yingshi Jin, Min Wu (Huntsman Chemistry R&D Center (Shanghai) Co., Ltd., China), Minseo Chae, Palwasha Jalalzai, Jihoon Seo, and Jin-Goo Park (Hanyang Univ., Korea)

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- ★[P-037] [Chemical and Mechanical Factors Contributing to Brush Nodule Mark Formation During Post-CMP Cleaning](#)

Sumit Kumar, Jae-Hyeong Lee, Yeon-Je Gye, Tae-Gon Kim, Jihoon Seo, and Jin-Goo Park (Hanyang Univ., Korea)

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- [P-038] [A Counter-Intuitive Strategy for Defect Control in Poly-Si CMP: Eliminating Wafer Rinse to Reduce Residue Defects](#)

Yinghao Bai, Mingkang Wang, Yixian Yao, Li Chieh Hsu, Hung-Chieh Chao, and Chang Hung Kung (Sien Integrated Circuit Co., Ltd., China)

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- [P-039] [Green Chemistry For Post Cu-CMP Cleaning To Replace Hazardous Chemicals Such As TMAH and Azole Based Inhibitors](#)

Kunhee Park, Yongho Jeong, Youngtaek Hong, and Jae-Dong Lee (KCTech Material R&D Center, Korea)

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- ★[P-040] [Adsorption and Loading Mechanisms of Metal Ions on PVA Brushes during Post-CMP Cleaning: Experimental and DFT Insights](#)

Maheepal Yadav, Sanjay Bisht, Jihoon Seo, Tae-Gon Kim, and Jin-Goo Park (Hanyang Univ., Korea)

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- ★[P-041] [In-Situ Electrochemical Investigation of Cu Tribocorrosion during PVA Brush Scrubbing](#)

Sanjay Bisht, Jiho Seo, Maheepal Yadav, Hyounggeun Kang, Tae-Gon Kim, Jihoon Seo, and Jin-Goo Park (Hanyang Univ., Korea)

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- ★[P-042] [Effects of Amino Acid Additives on Tungsten Surface Behavior during Post-CMP Cleaning](#)

Changshou Jin, Geumji Back, and Taesung Kim (Sungkyunkwan Univ., Korea)

★[P-043] [In-situ Conditioning Optimization for Slurry Residue Contamination Control in CMP Wafer Rinse Step](#)

Hyun-jin Jeong (Sungkyunkwan Univ. and SK hynix, Korea), Minju Lee, Kyeongtae Hong (SK hynix, Korea), and Taesung Kim (Sungkyunkwan Univ. and SAINT, Korea)

[P-044] [Metal Compatible Ceria Post-CMP Cleans](#)

Volley Wang, Fred Huang, and Ray Yang (Qnity Electronics Inc., Taiwan)

[P-045] [Suppressing Particle Contamination and Mechanical Damage in CMP via Uniformly Distributed Pad Asperities](#)

Hyun Jun Ryu, Seounghee Yun, Hyeongmin Je, and Sanha Kim (KAIST, Korea)

★[P-046] [Investigation of Abrasive Particle Size Effects on Mo CMP and GDWBased Cleaning Performance](#)

Seoyul Geum, Woogyung Jeon, and Taesung Kim (Sungkyunkwan Univ., Korea)

[P-047] [A Predictive AFM Adhesion Force Method for PCMP Cleaning Efficiency](#)

Ray Chen, Fred Huang, Jacky Cheng, Peter Sun, and Ping Hsu (Qnity Electronics Inc., Taiwan)

[P-048] [Investigation of Factors Affecting Brush Self-Cleaning Performance in Post-CMP Cleaning](#)

Masamitsu Kurashita, Natsuko Urushihara (EBARA Corp., Japan), Jin-Goo Park (Hanyang Univ., Korea), and Hirokuni Hiyama (EBARA Corp., Japan)

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- [P-049] [Electrochemical and Q-Time Integrated Methodology for Screening Cu Surface Stability in Post-CMP Cleaning](#)

Fred Huang, Jacky Cheng, Peter Sun, and Ping Hsu (Qnity Electronics Inc., Taiwan)

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- ★[P-050] [Influence of Chelating Agents on Mo-Ion Mediated Silica Adhesion to PVAc Brushes during the Mo Post-CMP Cleaning Process](#)

Minjun Son, Sumit Kumar, Soonmin Lee, Gyeongwon Lee, Tae-Gon Kim (Hanyang Univ., Korea), Junsang Lee, Gayoung Kim, In-Kwon Kim, Sangkyun Kim (Samsung Electronics Co., Ltd., Korea), Jihoon Seo, and Jin-Goo Park (Hanyang Univ., Korea)

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- ★[P-051] [Enhancing Cu Recess Controllability via Additive-Modulated Post-CMP Cleaning for Hybrid Copper Bonding](#)

Arim Woo, Jun-Hee Han, Jin-Goo Park, Jihoon Seo, and Tae-Gon Kim (Hanyang Univ., Korea)

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- [P-052] [Ceria-Induced Particle Defects Formation and a New Post-CMP Cleaning Strategy to Improve Yield](#)

Shu-Yi Meng, Ying-Pei Huang, Yu-Yun Cheng, Yu-Fang Yeh, Chia-Wei Wang, Wei-En Huang, and Ping Hsu (Qnity Electronics Inc., Taiwan)

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- [P-053] [Mechanism Study of pH Shock Effect for Organometallic Residue Formation in PCMP Process](#)

Jacky Cheng, Mi-Jen Kuo, Peter Sun, and Ping Hsu (Qnity Electronics Inc., Taiwan)

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- ★[P-054] [Impact of Megasonic Conditions on Dishing Variation and Damage during Post-CMP H₂-DIW Cleaning for Hybrid Copper Bonding](#)

Jun-Hee Han, Arim Woo, Ji-An Lee, Jin-Goo Park, Jihoon Seo, and Tae-Gon Kim (Hanyang Univ., Korea)

[P-055] [Cu Post CMP Cleaning Defect Control: Hillock Prevention and Surface State Control](#)

[Lily Jiang](#), Bing Liu, and Libbert Peng (Anji Microelectronics Co., Ltd., China)

★[P-056] [Effect of Post-CMP Cleaning Methods on Cu Pad Dishing and Cleaning Efficiency for Hybrid Cu Bonding](#)

[Seungjun Lee](#), Junhee Han, Arim Woo, Jin-Goo Park, Ji-Hoon Seo, and Tae-Gon Kim (Hanyang Univ., Korea)

★[P-057] [Evaluation of PVA Brush Cleaning for Improving Surface Cleanliness and Topography Uniformity of 4H-SiC Substrates](#)

[Ji-An Lee](#), Jun-Hee Han, Arim Woo, Ji-Hoon Seo, Jin-Goo Park, and Tae-Gon Kim (Hanyang Univ., Korea)

★[P-058] [Decoupling Cu Protection and Residual Adhesion of Organic Inhibitors in TMAH-Based Cu Post-CMP Cleaning](#)

[Minseo Chae](#), Tae-Gon Kim, Ji-hoon Seo, and Jin-Goo Park (Hanyang Univ., Korea)

★[P-059] [Post-CMP Cleaning of Ceria Abrasive Particles Removal from High-Quality 4H-SiC Surfaces](#)

[Jin Xu](#), Boao Ma, Bowen Luo, and Xin-Ping Qu (Fudan Univ., China)

★[P-060] [Hydrogen Nanobubble Water Assisted Post-CMP Cleaning of Mesoporous Ceria Particles on SiO₂](#)

[Boao Ma](#), Xuhao Cao, Bowen Luo, Jin Xu, Linyi Shen (Fudan Univ., China), Lijuan Zhang (CAS, China), and Xin-Ping Qu (Fudan Univ., China)

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- ★[P-061] [Three-Dimensional Position Tracking of 100 nm Silica Nano-Particles in Shear Flow Using Evanescent and Dark-Field](#)

Shin Tanihara, Panart Khajornrungruang, Ryunosuke Yamagata (Kyushu Inst. of Tech., Japan), Natsuko Urushihara, Tomoya Nishi, and Hirokuni Hiyama (EBARA Corp., Japan)

■ 05. AI & ML for CMP / Process Control

- [P-062] [Semi-Automated Topography Analysis for Post-CMP Surface Planarity Assessment](#)

Daniel Chang, Syin Hsu, Sunny Chan, and Tracy Lin (Qnity Electronics Inc., Taiwan)

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- ★[P-063] [Study on AI-Assisted CMP Removal Rate Prediction Using Integrated Process Data and Cerium Carbonate-Based Slurry](#)

Eunseo Woo, Sohee Hwang (Hannam Univ., Korea), Jaeyoung Jung (ETRI, Korea), and Woonjoong Kim (Hannam Univ., Korea)

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- ★[P-064] [Performance Evaluation of Data-Driven Predictive Models for CMP Material Removal Rate](#)

Jaewook Lee, Incheol Ha, Bobin Kang, Gwanhun Song, Gitae Park, and Hyunseop Lee (Dong-A Univ., Korea)

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- [P-065] [Unconditional Spectral Latent Diffusion for CMP Sensor Time Series Augmentation and Material Removal Rate Prediction](#)

Taehyun Park, Donggi Yun, Sang-Jung Ra, Hakjong Shin (ETRI, Korea), Woonjung Kim (Hannam Univ., Korea), and Jaeyoung Jung (ETRI, Korea)

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- [P-066] [Digital-Twin-Assisted Evaluation of DOE Strategies for Zone-Wise Pressure-Removal Characterization in CMP](#)

Seungchoun Choi, Yonghwan Yim, and Semyeong Oh (Amously Inc., Korea)

■ 06. Metrology & Inspection / Equipment / Process Diagnostics

- ★[P-067] [Real-Time CMP Monitoring Using Miniaturized Eddy Current Sensors Embedded in Additively Manufactured Pad](#)

[Gunhoo Park](#), [Dong Geun Kim](#), [Seong Jae Kim](#), and [Sanha Kim](#) (KAIST, Korea)

- [P-068] [Inline Real-Time Monitoring of Hydrogen Peroxide Concentration in CMP Slurries Using Ultrasonic Technology for Advanced Process Control](#)

[Raymond Maas](#) (Rhosonics Analytical B.V., The Netherlands)

- [P-069] [The Role of Pump Technology in Maintaining CMP Slurry Health for Advanced Node Manufacturing](#)

[Gary Van Schooneveld](#) and [Mark Litchy](#) (CT Associates, Inc., USA)

- [P-070] [Challenges and Opportunities of Recycled Slurry Metrology](#)

[Rashid Mavliev](#) (Mavlipa LLC, USA), [Robert Rhoades](#) (Kothar Tech., USA), and [Knut Gottfried](#) (ErzM-Tech., Germany)

- ★[P-071] [Estimation of Pad Uniformity by Diamond Conditioning with Overlapped Areas Method for Advanced CMP Process](#)

[Kai-Min Tian](#), [Chao-Chang A. Chen](#), [Wan-Hsiang Tseng](#) (Nat'l Taiwan Univ. of Science and Tech., Taiwan), [Manabu Tsujimura](#), [Hirokuni Hiyama](#), and [Naoyuki Handa](#) (EBARA Corp., Japan)

- ★[P-072] [Study of 3D Pad Microstructure Models with Representative Volume Element and Micro-CT Reconstruction](#)

[Pai-Hsiang Chao](#), [Chao-Chang A. Chen](#), and [Le Nam Quoc Huy](#) (Nat'l Taiwan Univ. of Science and Tech., Taiwan)

■ 07. CMP Consumables (Slurry, Abrasive, Pad, Conditioner, Filter etc.)

[P-073] [Precision Sintered Diamond Conditioners with Controlled Tip Coplanarity for Enhanced CMP Stability](#)

Felix Lin, Flora Chang, Ping-He Chen, and [Jeffrey Yeh](#) (3M Company, Taiwan)

[P-074] [Next Generation of Fine Particle Count \(FPC\) Reduction Filter](#)

[Henry \(Yu-Heng\) Cheng](#), Yuxin Li, Alan Chao, Enzo Chen, Howard Shih, Aiden Chang, Ying Qi, and Henry Wang (Entegris, Inc., Taiwan)

[P-075] [Impact of Material and Structural Properties of Silica Particle on SiO₂ Removal Rate](#)

[Yuichi Watanabe](#), Shota Suzuki, and Tsukuru Ohwaki (Fujimi Inc., Japan)

[P-076] [Research on Nano Ceria Slurry](#)

[Kaiqiang Wang](#), Qidong Zhang, Nannan Zhang, Wen Zheng, Hung-Chieh Chao, and Chang Hung Kung (Sien Integrated Circuit Co., Ltd., China)

[P-077] [From Lab to Fab: Comparative Study of CMP Filtration Requirements in FEOL and Advanced Packaging Processes](#)

[Chloe \(Ting-Chen\) Chen](#), Alex Chuang, Mott Chien, Hager Yeh, Jason Fu, and YiWei Lu (Entegris. Ltd., Taiwan)

[P-078] [Oxidation-Selective Chemically Controlled CMP Strategy for Molybdenum-Tungsten Integration in Advanced MOL Contacts](#)

[James Hsu](#) and Joseph Sung (Qnity Electronics, Inc., Taiwan)

★[P-079] [Effects of Pad Thermal Properties on CMP Behavior of Molybdenum: Difference between Soft Pad and Hard Pad](#)

[Woogyung Jeon](#) and Taesung Kim (Sungkyunkwan Univ., Korea)

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- [P-080] [Improving Wafer Defects and Enhancing Production Efficiency through Optimized Filter Design and Application \(CMP Consumable\)](#)

Jinhyuk Lim, Youna Kim, Donghyun Kim, and Jaehwan Kim (SK hynix Inc., Korea)

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- [P-081] [Radial Mapping of CMP Pad Conditioner Performance via Optical Haze Measurement on Sacrificial Polymer Films](#)

Ping Chuang (Nippon Alloy Co., Ltd., Taiwan)

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- [P-082] [Design for Silicon Stop System Using Anionic Silica System](#)

Moeka Ajiki, Sora Shirai (Fujimi Corp., Japan), Sunshine Wei (Fujimi Corp., Taiwan), Ryota Mae, Shogo Onishi, and Tatsuhiko Hirano (Fujimi Corp., Japan)

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- [P-083] [Particle Size Dependence of CeO₂ Slurry on Oxide Chemical Mechanical Planarization Material Removal Rate](#)

Haiying Yu, Yixian Yao, Yinghao Bai, and Chang Hung Kung (Sien Integrated Circuit Co., Ltd., China)

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- [P-084] [Filtration Technologies and Solutions for CMP Process Optimization](#)

Sanghyun Bae, Yunseo Jang, Jeongmok Cho, and Daniel Eumine Suk (SYNOPEX Inc., Korea)

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- [P-085] [New Method for Slurry Filter Selection to Secure Industrial Deployment](#)

Clément Castan, Victor Soty, Samson Toviho, Maryline Cordeau, Joseph Antoine (Univ. Grenoble Alpes, France), Paola Gonzalez Aguirre, Federico Barbieri, Günter Haas, Patrick O'Hagan (Entegris, France), Aurore Bonneval, Silvio Del Monaco (STMicroelectronics, France), and Catherine Euvrard (Univ. Grenoble Alpes, France)

[P-086] [High Removal Rate Ceria Abrasives](#)

Manabu Yuasa, Eisaku Suda, Takao Sekimoto, Akihisa Matsumoto (Solvay Special Chem Japan, Ltd, Japan), François Gombault, and Réka Toth (Solvay - Rhodia Opérations, France)

★[P-087] [Structured Surface Pads for High-Efficiency STI Planarization](#)

Youngwook Park, Yeongjeong Kang, Taekyung Lee, Doyeon Kim, and Hanchul Cho (KITECH, Korea)

[P-088] [New CMP Pads for Advanced Technologies](#)

Jae Eung Koo, Ravichandra Palaparthi, Grant Hou, and Dave Hui (Qnity Electronics Inc., USA)

[P-089] [Investigation of Selective and Non-Selective Niobium CMP for Quantum Applications](#)

Floriane Baudin, Cassandre Beluffi, Sebastien Dominguez, Richard Souil, Candice Thomas, Pablo Renaud, and Catherine Euvrard (Univ. Grenoble Alpes, France)

[P-090] [Development of an Optimized Pad Conditioner Replacement Procedure for an EBARA FREX200 M2 CMP Tool](#)

Andreas Krüger, Awwal Adeniyi Adesunkanmi, and Marco Lisker (IHP, Germany)

[P-091] [Breakthrough CMP Pad Designs: New Surface Textures for Advanced IC](#)

Rachel Ma, Jessica Lindsay, Weisi Li, Kevin P. Dockery, and Aaron Peterson (Entegris. Ltd., USA)

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- [P-092] [Improvement of Soft Pad Conditioning by Advanced Conditioner Design – FPC \(Flexible Pad Conditioner\)](#)

Changwan Bae (3M Company, Korea), Uma Rames Krishna Lagudu, Thomas Mooney (3M Company, USA), and Yongsuk Yang (3M Company, Korea)

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- ★[P-093] [Effect of Ultrafine Bubbles on Polishing Pad Lifetime In Silicon CMP](#)

Kota Takahashi (Gifu Univ. and Mitsubishi Chemical Engineering Corp., Japan) and Michio Uneda (Gifu Univ., Japan)

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- ★[P-094] [Aerosol Metrology-Based Inline Evaluation of CMP Slurry Filter](#)

Seongmin Cho (Seoul Nat'l Univ. of Science and Tech., Korea), Daniel R. Troolin, Andrea J. Tiwari (TSI Incorporated, Shoreview, USA), and Dong-Bin Kwak (Seoul Nat'l Univ. of Science and Tech., Korea)

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- ★[P-095] [Study on the Synthesis of Ceria Nanoparticles for Semiconductor CMP Using a Flow Reactor System](#)

Tao Lyu, Sohee Hwang, Sooyeon Choi, and Woonjung Kim (Hannam Univ., Korea)

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- ★[P-096] [Study on Ceria Slurry Using Modified Cerium Carbonate for Semiconductor CMP process](#)

Jaeyeong Cho, Sohee Hwang, Seyoung Ahn, and Woonjung Kim (Hannam Univ., Korea)

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- [P-097] [Innovative Microreplicated CMP Pad with Advanced Gel Subpad Architecture for Enhanced Edge Profile and Planarization Temperature Control](#)

Don Kim (3M Korea, Korea), Yi He, Duy K. LeHuu (3M USA, USA), YongSuk Yang, YoongHee Na, and Changwan Bae (3M Korea, Korea)

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- ★[P-098] [CMP Slurry Design for Controlling Surface Profiles in Cu/SiO₂ Co-CMP for Hybrid Bonding](#)

Jihye Lim, Junhui Lee, Subin Son, and Jeong-Chul Kim (Hanbat National Univ., Korea)

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- ★[P-099] [Stabilizer Ratio Dependent Surface Reaction of Fe\(NO₃\)₃ Based Tungsten CMP Slurry](#)

Yeseung Choi, Hyunho Kim, Eun Cho, and Teasung Kim (Sungkyunkwan Univ., Korea)

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- [P-100] [Material Paradigm Shift of Polyurethane CMP Pads: Transition from Petrochemical to Sustainable Bio- and CO₂-Based Materials](#)

Jangwon Seo, Mingyoung Ji, Hajeong Kang, Jongwook Yoon, and Seungchul Hong (Enpulse Co., Ltd., Korea)

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- ★[P-101] [Study on the Synthesis of Anionic Polymer Dispersants for Improving Colloidal Stability of Ceria CMP Slurry](#)

Chaeyeon Kim, Sohee Hwang, Songhee Kim, and Woonjung Kim (Hannam Univ., Korea)

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- ★[P-102] [Design of Cu-Silica Composite Abrasives in CMP Slurry for High-Efficiency CMP](#)

Junhui Lee, Jihye Lim, and Jeong-Chul Kim (Hanbat Nat'l Univ., Korea)

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- ★[P-103] [Structure-Based MRR Modeling and Slurry Transport in SiO₂ CMP Using Micro-Patterned Pads](#)

Geumji Back and Taesung Kim (Sungkyunkwan Univ., Korea)

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- [P-104] [A Reactive Pad enabling Abrasive-free CMP: A Paradigm Shift in Planarization](#)

Matthias Stender (ChEmpower Corp., USA)

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- [P-105] [Improving CMP Slurry Filtration Efficiency through Optimized Wetting Techniques and Hydrophilic Depth Filters](#)

Yuya Takashima, Kentaro Fujita, and Minori Nishioka (Rokitechno Co., Ltd, Japan)

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- [P-106] [Improving CMP Slurry Defectivity Control through Membrane-Based Filtration: A Comparison with Conventional Depth Media Filters](#)

Majid Entezarian, John Morby, and Sandeep Singh (Thermo Fisher Scientific Inc., USA)

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Yongsik Moon, Kyoung-Kuk Kwack, Joohan Lee, Jongjae Lee, Eunhwa Song, Youngtae Jeon, Johee Lee, Sungyu Park, and Yujeong Jin (EHWA Diamond, Korea)

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- ★[P-108] [Low Contact Pressure CMP Using Surface-Structured Pads with Diverse 3D Asperity Architectures](#)

JunYoung Park, Seounghee Yun, Dong Geun Kim, Sukkyung Kang, Hyogun An, and Sanha Kim (KAIST, Korea)

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- ★[P-109] [Effect of Molecular Structure of Amino Acid Inhibitor on Corrosion and Polishing Behavior in W CMP](#)

Haemin Jeong, Hyeonjeong Lee, Seungmoon Choi, and Taesung kim (Sungkyunkwan Univ., Korea)

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- ★[P-110] [Development and Mechanistic Investigation of a Non-Azole Inhibitor System for Cu CMP Applications](#)

Eunseok Lee and Sangwoo Lim (Yonsei Univ., Korea)

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- ★[P-111] [Modeling and Experimental Validation of Soft Pad Surface Evolution with Optimal Pad Conditioning by Diamond Disk for Copper CMP Process](#)

[Po-Shen Chen](#), Chao-Chang A. Chen, Pai-Hsiang Chao, Chao-Sung Chang, WanHsiang Tseng (Nat'l Taiwan Univ. of Science and Tech., Taiwan), Jason Lin, Yi He, Kazuma Nuno, and Fay Salmon (3M, USA)

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- [P-112] [Enabling Next-Generation CMP Performance through Ultra-Pure WaterSoluble Polymers: The Critical Role of Molecular Weight Control, Process Consistency, and Trace Metal Reduction](#)

[Eric S. Moyer](#) (Polysciences, USA)

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[Natsuko Oshima](#), Kazuki Yagi, Tatsuhiko Hirano, and Kazumi Sugai (Fujimi Incorporated, Japan)

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[Damien Yiyuan Khoo](#) (Bruker (Malaysia) Sdn Bhd, Malaysia)

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[Te-Chun Wang](#), Lin-Chen Ho, Shang-Yuan Chen, and Ivan Li (Qnity™ Electronics Inc., Taiwan)

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[Guinea Niku](#), Ishii Tsubasa, and Masuya Koichi (EBARA Corp. Japan)

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Da-Shiuan Chiou (Qnity Electronics, Inc., Taiwan), Seda Aktas (Qnity Electronics, Inc., USA), Ivan Li (Qnity Electronics, Inc., Taiwan), and Ravi Palaparthi (Qnity Electronics, Inc., USA)

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Junil Cho, Byungsu Kim, and Taesung Kim (Sungkyunkwan Univ., Korea)

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Wonbin Ko, Geumji Back, and Taesung Kim (Sungkyunkwan Univ., Korea)

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